

Notice of References Cited

Application/Control No.

10/056,179

Applicant(s)/Patent Under
Reexamination
TAYLOR, THEODORE M.

Examiner

Howard Weiss

Art Unit

2814

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,376,877	04-2002	Yu et al.	257/315
	B	US-6,271,561	08-2001	Doan	257/316
	C	US-6,214,667	04-2001	Ding et al.	438/257
	D	US-6,153,494	11-2000	Hsieh et al.	438/211
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kobayashi, T., et al., "A 0.24- μ m sq. Cell Process with 0.18- μ m Width Isolation and 3-D Interpoly Dielectric Films for 1-Gb Flash Memories", Dec. 1997, IEDM 97, pp. 275-8
	V	Shirai, H., et al., "A0.54 μ m sq. Self-Aligned HSG Floating Gate Cell (SAHF Cell) for 256Mbit Flash Memories", Dec. 1995, IEDM 95, pp. 653-6
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.